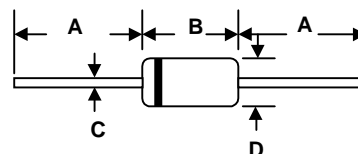


Silicon Epitaxial Planar Switching Diode

Applications

- High-speed switching

This diode is also available in MiniMELF case with the type designation LL4148



DO-35		
Dim	Min	Max
A	25.40	—
B	—	3.42
C	—	0.45
D	—	1.7
All Dimensions in mm		

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

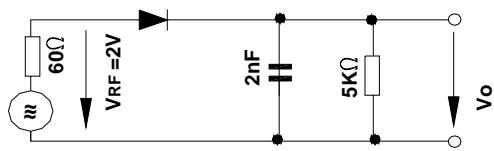
Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	100	V
Reverse Voltage	V_R	75	V
Average Rectified Forward Current	$I_{F(AV)}$	200	mA
Non-repetitive Peak Forward Surge Current	I_{FSM}	0.5	A
		1	
		4	
Power Dissipation	P_{tot}	500 ¹⁾	mW
Junction Temperature	T_j	200	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 200	$^\circ\text{C}$

¹⁾ Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature.

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 10\text{ mA}$	V_F	-	1	V
Leakage Current at $V_R = 20\text{ V}$ at $V_R = 75\text{ V}$ at $V_R = 20\text{ V}, T_j = 150\text{ }^\circ\text{C}$	I_R I_R I_R	- - -	25 5 50	nA μA μA
Reverse Breakdown Voltage at $I_R = 100\text{ }\mu\text{A}$ at $I_R = 5\text{ }\mu\text{A}$	$V_{(BR)R}$ $V_{(BR)R}$	100 75	- -	V V
Capacitance at $V_R = 0, f = 1\text{ MHz}$	C_{tot}	-	4	pF
Voltage Rise when Switching ON tested with 50 mA Forward Pulses $t_p = 0.1\text{ }\mu\text{s}$, Rise Time < 30 ns, $f_p = 5\text{ to }100\text{ KHz}$	V_{fr}	-	2.5	V
Reverse Recovery Time at $I_F = 10\text{ mA}$ to $I_R = 1\text{ mA}$, $V_R = 6\text{ V}$, $R_L = 100\text{ }\Omega$	t_{rr}	-	4	ns
Thermal Resistance Junction to Ambient Air	R_{thA}	-	0.35 ¹⁾	K/mW
Rectification Efficiency at $f = 100\text{ MHz}$, $V_{RF} = 2\text{ V}$	η_V	0.45	-	-

¹⁾ Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature.



Rectification Efficiency Measurement Circuit

